



GP1M010A080H Information



For Reference Only

Part Number GP1M010A080H

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 9.5A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP1M010A080H Specifications

Manufacturer Part Number GPIM010A080H Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 9.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 53nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2336pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 1.05 Ohm @ 4.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C9.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs53nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2336pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs1.05 Ohm @ 4.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
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Current - Continuous Drain (Id) @ 25°C9.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs53nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2336pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs1.05 Ohm @ 4.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs53nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2336pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs1.05 Ohm @ 4.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	9.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2336pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.05 Ohm @ 4.75A, 10V Operating Temperature John Company Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 2336pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.05 Ohm @ 4.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs1.05 Ohm @ 4.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	53nC @ 10V
FET Feature - 290W (Tc) Rds On (Max) @ Id, Vgs 1.05 Ohm @ 4.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	2336pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.05 Ohm @ 4.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs1.05 Ohm @ 4.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Power Dissipation (Max)	290W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	1.05 Ohm @ 4.75A, 10V
Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
•		Report errors?

GP1M010A080H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP1M010A080H Payment Methods



















GP1M010A080H Shipping Methods













If you have any question about GP1M010A080H, please do not hesitate to contact us!

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